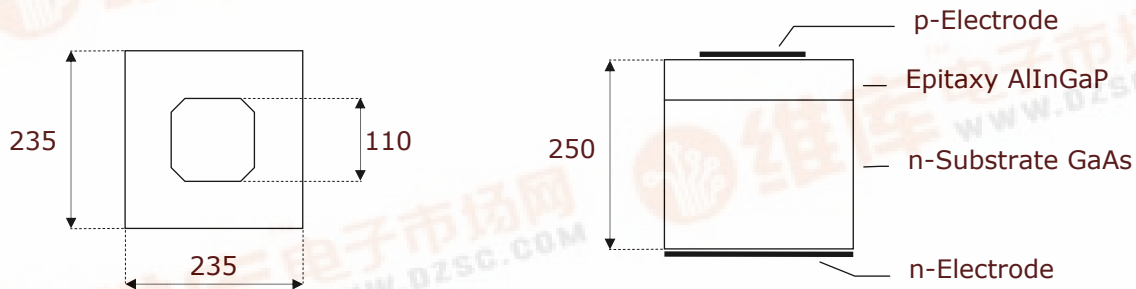




**YELLOW-GREEN Item No.: 160272**

1. This specification applies to AlInGaP / GaAs LED Chips
2. Structure
  - 2.1 Mesa structure
  - 2.2 Electrodes
 

p-side (anode)	Au alloy or Al
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	$V_F$	$I_F = 20 \text{ mA}$		2,10	2,40	V
Reverse current	$I_R$	$V_R = 5 \text{ V}$			10	$\mu\text{A}$
Luminous intensity *	$I_V$	$I_F = 10 \text{ mA}$		26,0		mcd
dom. wavelength	$\lambda_D$	$I_F = 20 \text{ mA}$		572		nm

\* On request, wafers will be delivered according to luminous intensity classes  
 Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire bond side on top  
 2) back contact on top

6. Labeling

Type	Lot No.	$I_V$ typ min max	Quantity
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